

Title (en)

EDGE-EMITTING SEMICONDUCTOR TUNABLE LASER

Title (de)

VERSTIMMBARER RANDEMITTIERENDER HALBLEITERLASER

Title (fr)

LASER ACCORDABLE EN SEMI-CONDUCTEUR A EMISSION PAR LA TRANCHE

Publication

**EP 1307955 A2 20030507 (FR)**

Application

**EP 01963053 A 20010802**

Priority

- FR 0102530 W 20010802
- FR 0010366 A 20000804

Abstract (en)

[origin: WO0213335A2] The invention concerns an edge-emitting semiconductor tunable laser (10) comprising a resonant cavity delimited by two reflectors (15, 20) one of which is fixed (15) and the other mobile (20), said cavity consisting of a first active gain section (1) with length L1 and a second tunable section of length L2. The invention is characterised in that the total length of the cavity L = to L1+L2 is not more than 20 mu m.

IPC 1-7

**H01S 5/14**

IPC 8 full level

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